

N-Ch MOSFET

General Description

The WSK160N15 is the highest performance trench N-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSK160N15 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

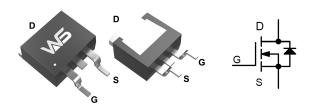
Product Summery

BVDSS	RDSON	ID
150V	6.6mΩ	160A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System

TO-263-2L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units	
V _{DS}	Drain-Source Voltage	150	V	
V_{GS}	Gate-Source Voltage	±20	V	
I _D	Continuous Drain Current, V _{GS} @ 10V(T _C =25 C)	160	Α	
I _{DM}	Pulsed Drain Current	550	Α	
EAS	Single Pulse Avalanche Energy	506	mJ	
P _D	Total Power Dissipation _C =25 ^ℂ)	210	W	
RθJA	Thermal resistance, junction-ambient	62	°C/W	
RθJC	Thermal resistance, junction-case	0.84	°C/W	
T _{STG}	Storage Temperature Range -55 to 155		$^{\circ}$	
T_J	Operating Junction Temperature Range	-55 to 155	${\mathbb C}$	



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	150			V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =30A		6.6	7.5	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250uA$	2.0	2.9	4.0	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =100V , V _{GS} =0V , T _J =25℃			1	uA
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$			±100	nA
Qg	Total Gate Charge	V _{DS} =50V , V _{GS} =10V , I _D =20A		72		nC
Q _{gs}	Gate-Source Charge			18		
Q_{gd}	Gate-Drain Charge			10		
T _{d(on)}	Turn-On Delay Time	- V _{DD} =50V , - V _{GS} =10V R _G =3Ω, - I _D =20A		22		
Tr	Rise Time			115		ns
T _{d(off)}	Turn-Off Delay Time			44		
T _f	Fall Time			105		
C _{iss}	Input Capacitance	V _{DS} =50V , V _{GS} =0V , f=1MHz		5240		
Coss	Output Capacitance			412		pF
C _{rss}	Reverse Transfer Capacitance			30		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V , Force Current			150	Α
I _{SM}	Pulsed Source Current ^{2,6}				500	Α
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =20A , T _J =25℃			1.3	٧

■ Note

- ¹) Repetitive rating; pulse width limited by max. junction temperature.
- 2) Pd is based on max. junction temperature, using junction-case thermal resistance.
- 3) The value of R0JA is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with Ta=25 °C.
- 4) VDD=50 V, RG=50 Ω , L=0.5 mH, starting Tj=25 °C.
- ⁵) Calculated continuous current based on maximum allowable junction temperature.



Typical Characteristics

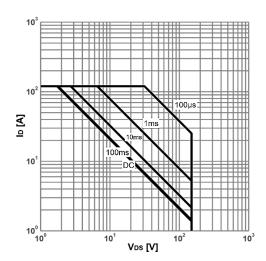


Figure 1. Power dissipation

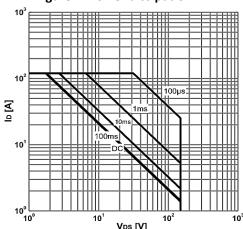


Figure 3. Safe operating area

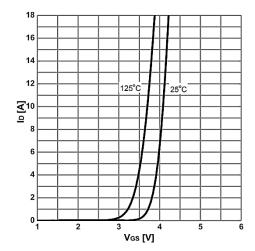


Figure 5. Typ. transfer characteristics

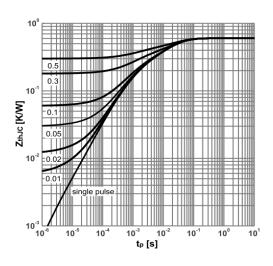


Figure 2. Max. transient thermal impedance

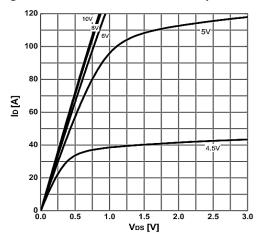


Figure 4. Typ. output characteristics

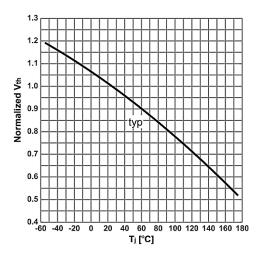


Figure 6. Gate threshold voltage vs. Junction Temperature





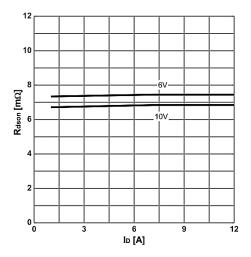


Figure 7. On-state resistance vs. Drain current

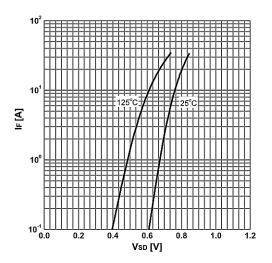


Figure 9. Forward characteristics of reverse diode

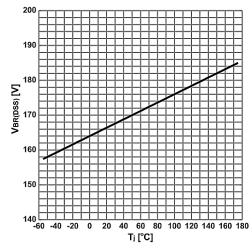


Figure 10: Breakdown Voltage Variation vs. Temperature

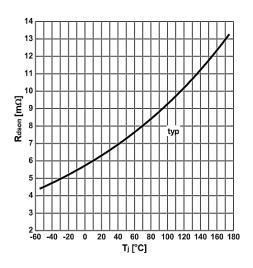


Figure 8. On-state resistance vs. Junction temperature

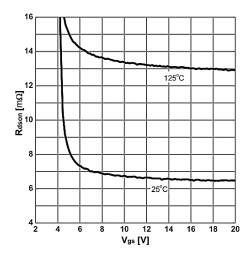


Figure 10. On-state resistance vs. Vgs characteristics

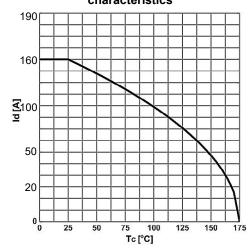


Figure 11: Maximum Drain Current



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DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7
STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1
DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1
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